

Applications

- High Voltage Supply & Pulsing
- Gate Threshold/Cutoff Voltage
- · Leakage Current

- Substrate Thermal Characterization
- Gate-to-Source & Gate-to-Drain Voltage
- Device Stress Testing

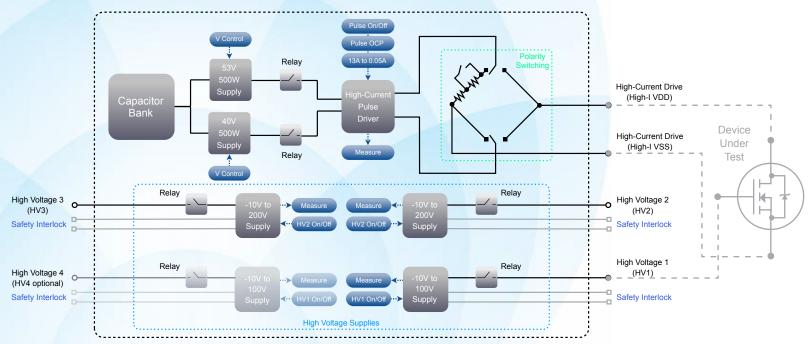
Overview

The RI8589 FET Pulser provides an all-in-one production solution for power device supply and parametric measurement. With a current drive and measurement range of 1μ A to 20A, this instrument enables evaluation of power FETs, BJTs, and IGBT devices as well as wide band-gap materials such as GaN and SiC. The RI8589 enables precise, small on-resistance measurements and 10μ s fast pulse capability for complete power device characterization, temperature stress, and failure analysis.

Key Features

- DC Parametric Measure & High-Power Supply in One Instrument
- High-Power Polarity Switching without Re-Cabling
- 10µs Burst, 1kW High Power Pulse Capability
- 8 Control Pins for External Relays

Block Diagram







RI8589 - High Power Supply/Pulser

Cassini Instrument Profile

Performance

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Supply	Gate Bias (HV1 HV3)	Drain Bias (HV2)	Drain Pulsing	Drain Reverse Diode Test
Image 10 mA 10 mA 23A 10A Settling Time 10 μs 10 μs 10 μs to 100ms (pulse) 10 μs Measure Image 1 μA to 20 mA 1 μA to 20 mA 1 μA to 20 mA 10 mA to 23 A -10mA to +10 mA to +10 mA Accuracy 0.1 % 0.2 % 0.3 % 0.1 % 0	V _{MAX} V _{MIN}	+80 V -10 V	185 V -5V	52V 8 V	+1V -5V
MAX Settling Time 10 μs 10 μs 10 μs to 100ms (pulse) 10 μs Measure 10 μs 10 μs 10 μs to 100ms (pulse) 10 μs Range 1 μA to 20 mA 1 μA to 20 mA 1 μA to 20 mA 10 mA to 23 A -10mA to +10m Accuracy 0.1 % 0.2 % 0.3 % 0.1 % Meas. Rate 80 ksps 80 ksps 80 ksps 80 ksps	V_{SET} Resolution	5 mV	20 mV	20 mV	-
Measure 1 μA to 20 mA 1 μA to 20 mA 1 μA to 20 mA 10 mA to 23 A -10 mA to +10	I _{MAX}	10 mA	10 mA	23A	10A
Range 1 μA to 20 mA 1 μA to 20 mA 1 μA to 20 mA 10 mA to 23 A -10 mA to +10 mA Accuracy 0.1 % 0.2 % 0.3 % 0.1 % Meas. Rate 80 ksps 80 ksps 80 ksps 80 ksps	Settling Time	10 µs	10 µs	10 µs to 100ms (pulse)	10 µs
Accuracy 0.1% 0.2% 0.3% 0.1% Meas. Rate 80 ksps 80 ksps 80 ksps 80 ksps 80 ksps	Measure				
Meas. Rate 80 ksps 80 ksps 80 ksps 80 ksps 80 ksps	Range	1 µA to 20 mA	1 µA to 20 mA	10 mA to 23 A	-10mA to +10mA
	Accuracy	0.1 %	0.2 %	0.3 %	0.1%
R _{out} 100 Ω 1 kΩ ¹ 100 Ω 1 kΩ ¹ 0.04 Ω 2.5 Ω	Meas. Rate	80 ksps	80 ksps	80 ksps	80 ksps
	R _{OUT}	100 Ω 1 kΩ¹	100 Ω 1 kΩ¹	0.04 Ω	2.5 Ω

Inputs/Outputs

High-Current Drive (High-I VSS)

High Voltage 1,2,3: (HV1/HV2/HV3) Output Drive/Rtn, Sense, Safety Interlock (HV4 optional)



Cassini Test Systems

A versatile, high-speed, automated test solution for analog, mixed-signal, RF, and millimeter-wave devices.

Cassini provides a modular base architecture that is fully configurable via Test Instrument Modules (TIMs) to meet the needs of any IC, wafer, or module test requirement.

Each TIM contains internally-cooled, RF-shielded instrumentation, signal distribution, and blind mate interfacing to provide targeted test resources and integrate to build up a complete production test platform.

Combined with Roos Instruments' integrated test software, Cassini can be configured to any application for maximum performance, true low cost of test, and the industry's fastest test times.

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 $^1 Current$ measurements below 100 μA use 1 k Ω

High-Current Drive (High-I VDD)

Relay Control Bits: GND pin, 8 Independent Control Lines, and +12V pin (optional)